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Fax Cover Sheet

DATE:

February 8, 2002

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Message

DOCKET GS 134

Please see attached Response to Restriction Requirement.

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Hshieh et al.

Scrial No.:

09/881,254

Filed:

June 14, 2001

Title:

Symmetric Trench MOSFET Device and Method of Making Same

Art Unit:

2826

Examiner:

Johannes P. Mondt

Docket No.:

GS 134

Assistant Commissioner for Patents

Washington, D.C. 20231

RESPONSE TO RESTRICTION REQUIREMENT

Sir:

In response to the Office Action dated January 9, 2002 (Paper No. 3), kindly consider the following response to the outstanding restriction requirement.

REMARKS

Claims 1-24 are pending in the application. Restriction was required to the following allegedly distinct inventions:

- I. Claims 1-16, drawn to a field effect transistor, classified in class 257, subclass 213.
- 11. Claims 17-24, drawn to a method of making a field effect device, classified in class 438, subclass 192.